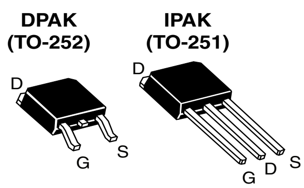
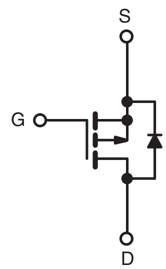
THE DATASHEET OF

IRFR9214TRLPBF

Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 250	
$R_{DS(on)}$ (Ω)	V_{GS} = - 10 V	3.0
Q_g (Max.) (nC)	14	
Q_{gs} (nC)	3.1	
Q_{gd} (nC)	6.8	
Configuration	Single	





P-Channel MOSFET

FEATURES

- P-Channel
- Surface Mount (IRFR9214, SiHFR9214)
- Straight Lead (IRFU9214, SiHFU9214)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE Available

DESCRIPTION

Third generation power MOSFETs from Vishay utilize advanced processing techniques to achieve low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.
The DPAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU, SiHFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 W are possible in typical surface mount applications.

ORDERING INFORMATION				
Package	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	IPAK (TO-251)
Lead (Pb)-free and Halogen-free	SiHFR9214-GE3	SiHFR9214TRL-GE3	SiHFR9214TR-GE3	SiHFU9214-GE3
Lead (Pb)-free	IRFR9214PbF	IRFR9214TRLPbF[a]	IRFR9214TRPbF[a]	IRFU9214PbF
	SiHFR9214-E3	SiHFR9214TL-E3[a]	SiHFR9214T-E3[a]	SiHFU9214-E3

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	- 250	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at - 10 V	T_C = 25 °C	I_D	- 2.7	A
		T_C = 100 °C		- 1.7	
Pulsed Drain Current[a]			I_{DM}	- 11	
Linear Derating Factor				0.40	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	100	mJ
Repetitive Avalanche Current[a]			I_{AR}	- 2.7	A
Repetitive Avalanche Energy[a]			E_{AR}	5.0	mJ
Maximum Power Dissipation	T_C = 25 °C		P_D	50	W
Peak Diode Recovery dV/dt[c]			dV/dt	- 5.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)[d]	for 10 s			260	

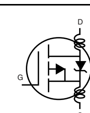
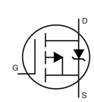
Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Starting T_J = 25 °C, L = 27 mH, R_g = 25 Ω, I_{AS} = - 2.7 A (see fig. 12).
c. $I_{SD} \leq$ - 2.7 A, dI/dt $\leq$ 600 A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq$ 150 °C.
d. 1.6 mm from case.

THERMAL RESISTANCE RATINGS					
PARAMETER	**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	-	110	°C/W
Maximum Junction-to-Ambient (PCB Mount)[a]	R_{thJA}	-	-	50	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	-	2.5	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 μA	- 250	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = - 1 mA	-	- 0.25	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 μA	- 2.0	-	- 4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 250 V, V_{GS} = 0 V	-	-	- 100	μA
		V_{DS} = - 200 V, V_{GS} = 0 V, T_J = 125 °C	-	-	- 500	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = - 10 V; I_D = - 1.7 A[b]	-	-	3.0	Ω
Forward Transconductance	g_{fs}	V_{DS} = - 50 V, I_D = - 1.7 A	0.9	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 25 V, f = 1.0 MHz, see fig. 5	-	220	-	pF
Output Capacitance	C_{oss}		-	75	-	
Reverse Transfer Capacitance	C_{rss}		-	11	-	
Total Gate Charge	Q_g	V_{GS} = - 10 V; I_D = - 1.7 A, V_{DS} = - 200 V, see fig. 6 and 13[b]	-	-	14	nC
Gate-Source Charge	Q_{gs}		-	-	3.1	
Gate-Drain Charge	Q_{gd}		-	-	6.8	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 125 V, I_D = - 1.7 A, R_g = 21 Ω, R_D = 70 Ω, see fig. 10[b]	-	11	-	ns
Rise Time	t_r		-	14	-	
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	
Fall Time	t_f		-	17	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	- 2.7	A
Pulsed Diode Forward Current[a]	I_{SM}		-	-	- 11	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = - 2.7 A, V_{GS} = 0 V[b]	-	-	- 5.8	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = - 1.7 A, dI/dt = 100 A/μs[b]	-	150	220	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	870	1300	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

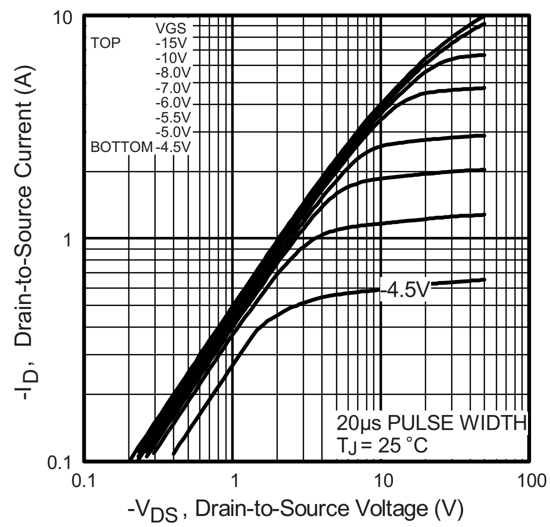


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

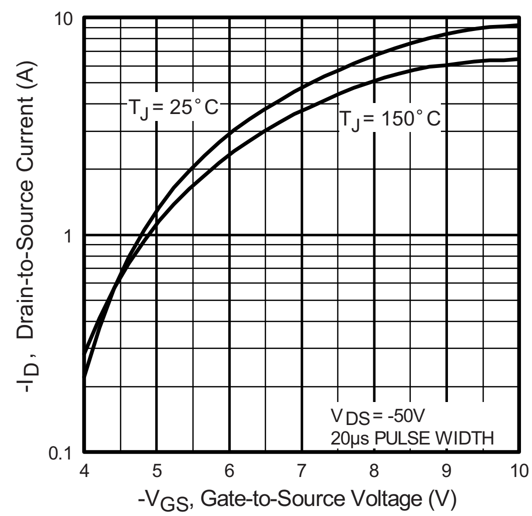


Fig. 3 - Typical Transfer Characteristics

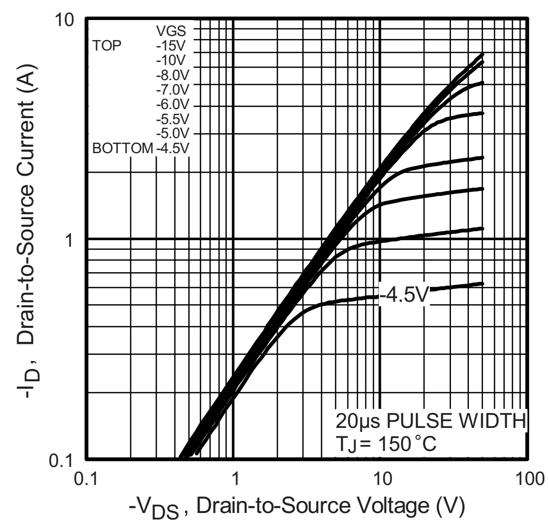


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

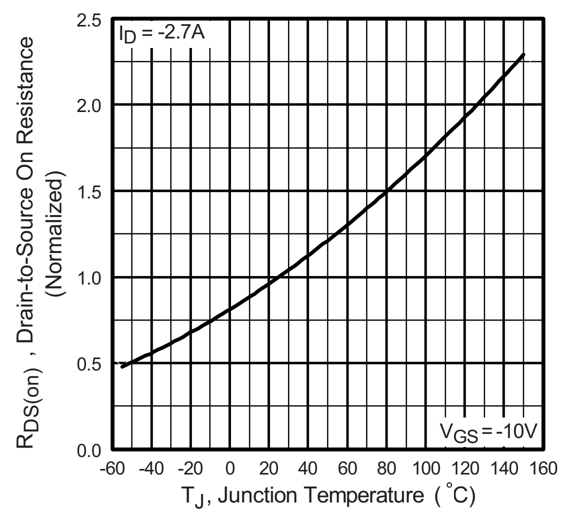


Fig. 4 - Normalized On-Resistance vs. Temperature

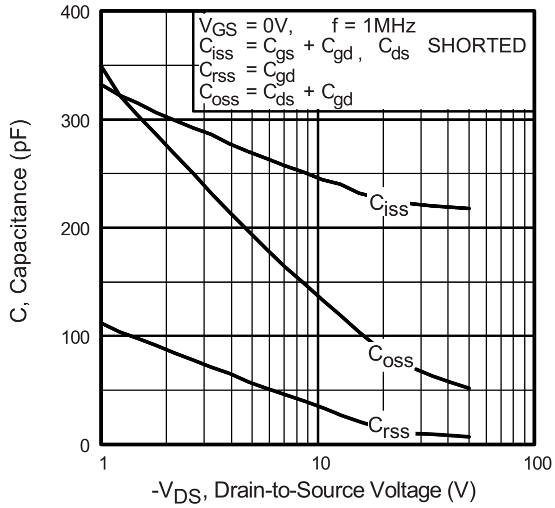


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

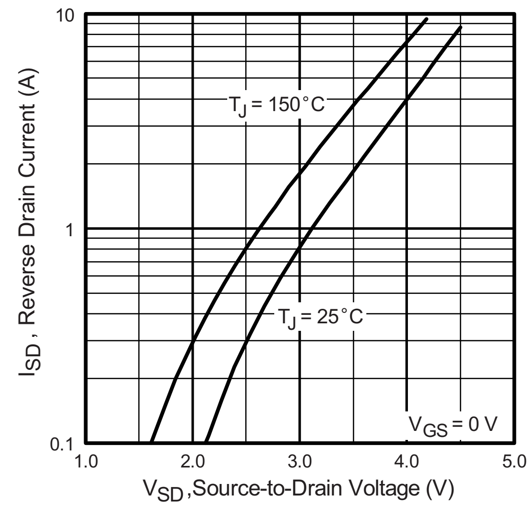


Fig. 7 - Typical Source-Drain Diode Forward Voltage

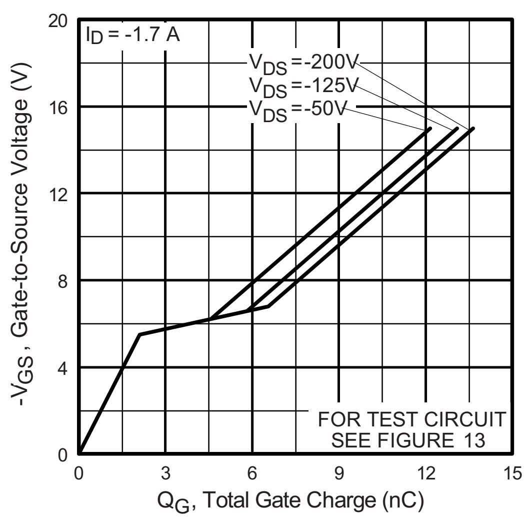


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

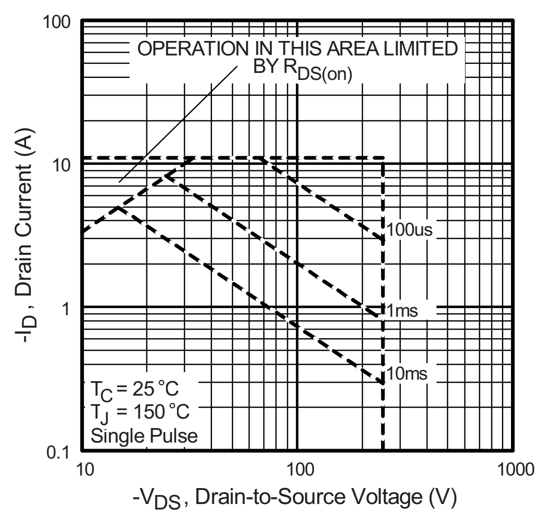


Fig. 8 - Maximum Safe Operating Area

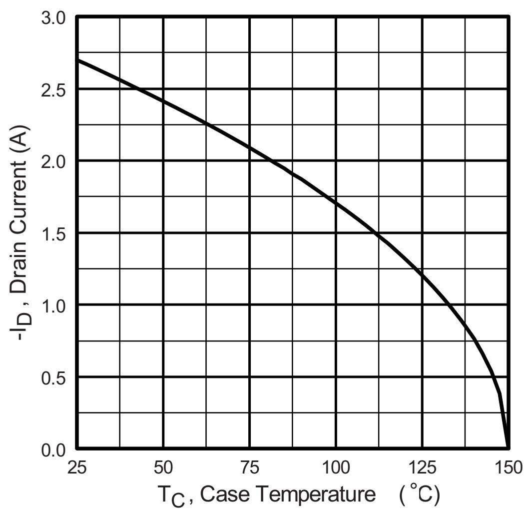


Fig. 9 - Maximum Drain Current vs. Case Temperature

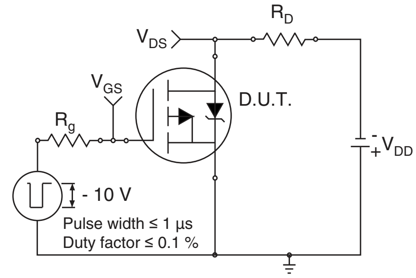


Fig. 10a - Switching Time Test Circuit

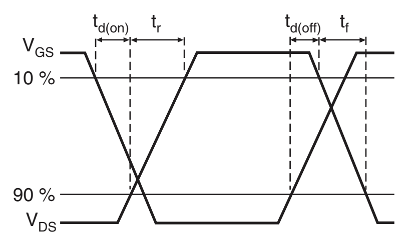


Fig. 10b - Switching Time Waveforms

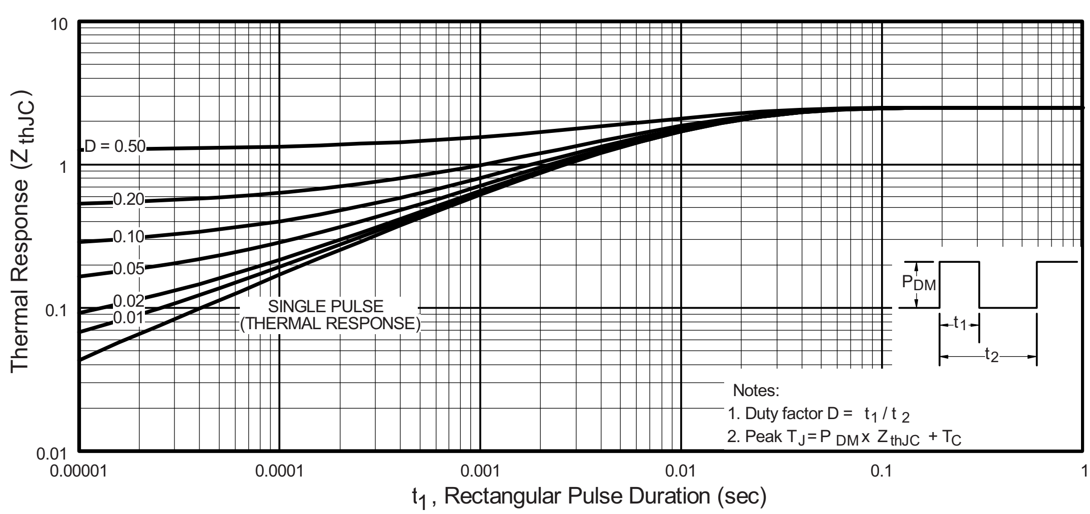


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

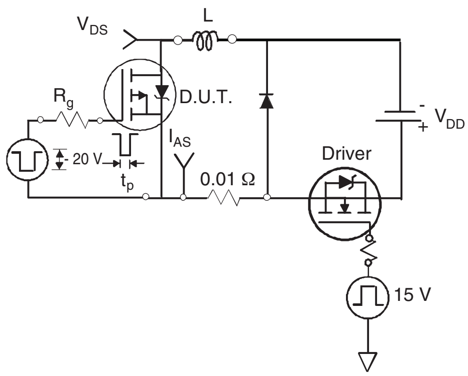


Fig. 12a - Unclamped Inductive Test Circuit

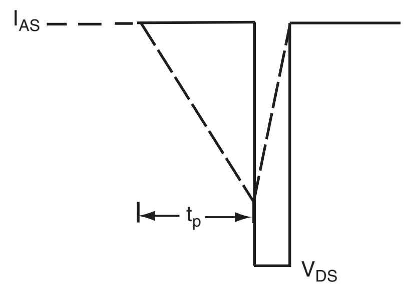


Fig. 12b - Unclamped Inductive Waveforms

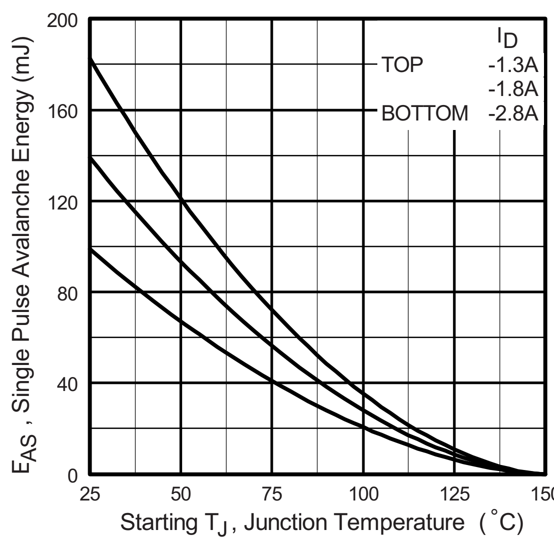


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

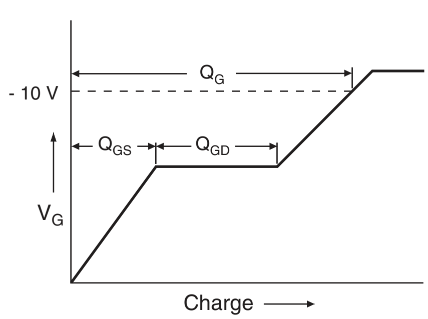


Fig. 13a - Basic Gate Charge Waveform

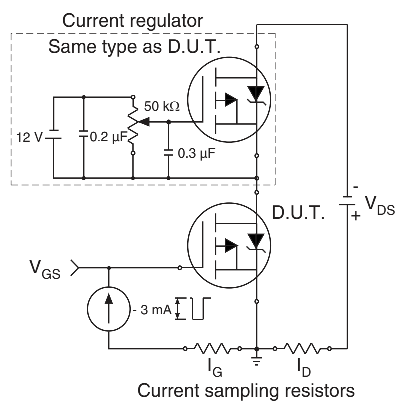
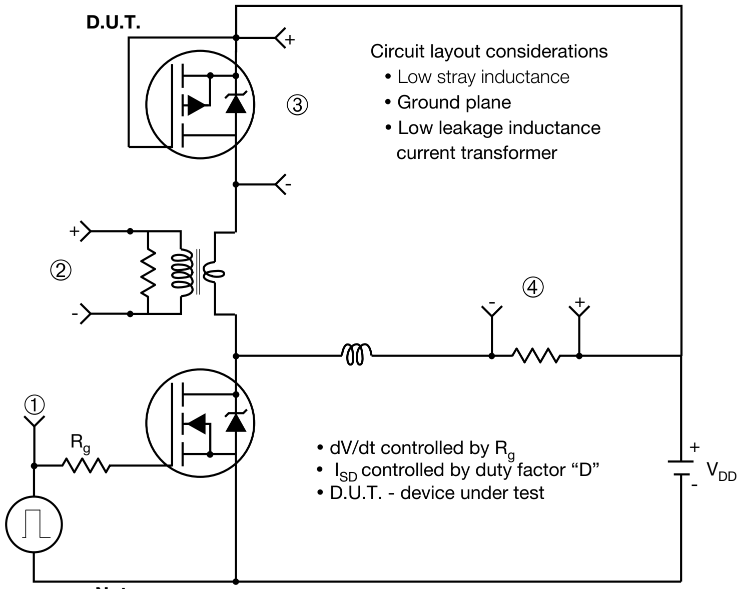
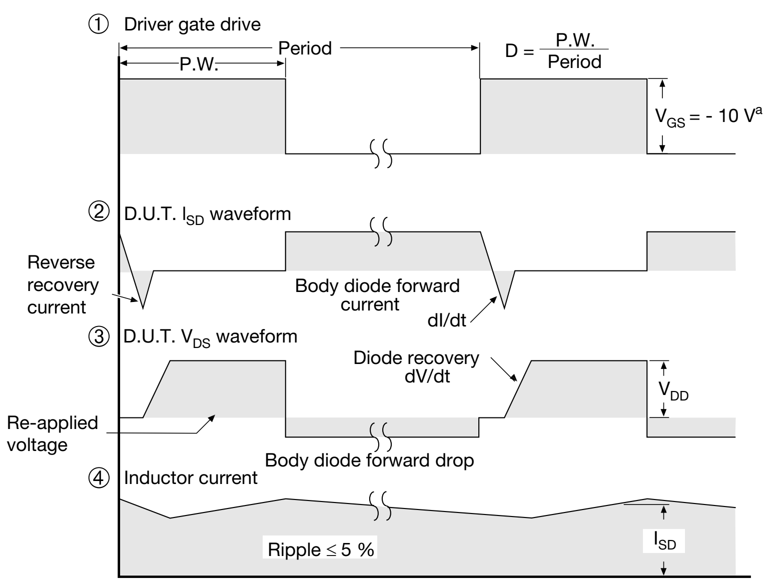


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note
• Compliment N-Channel of D.U.T. for driver

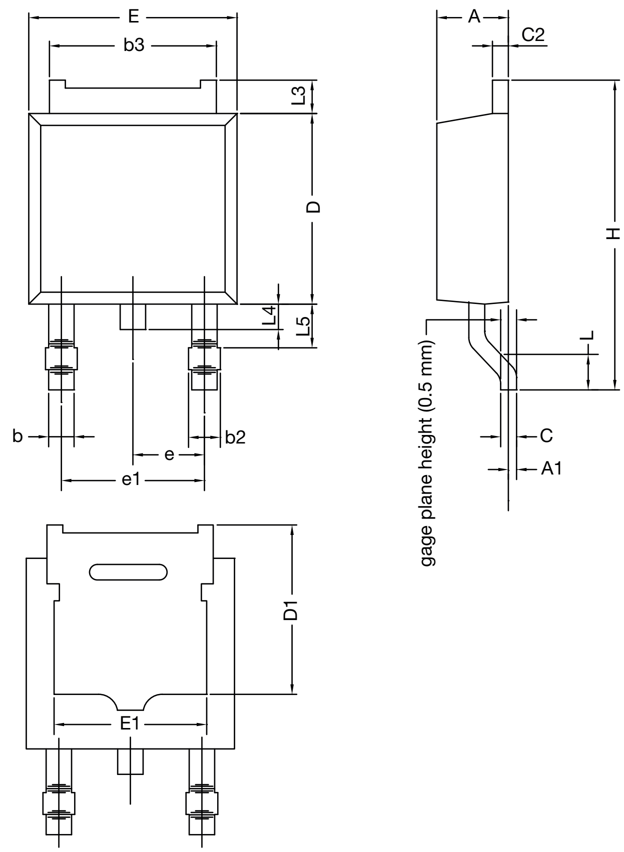


Note
a. V_{GS} = - 5 V for logic level and - 3 V drive devices

Fig. 14 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91282.

TO-252AA Case Outline

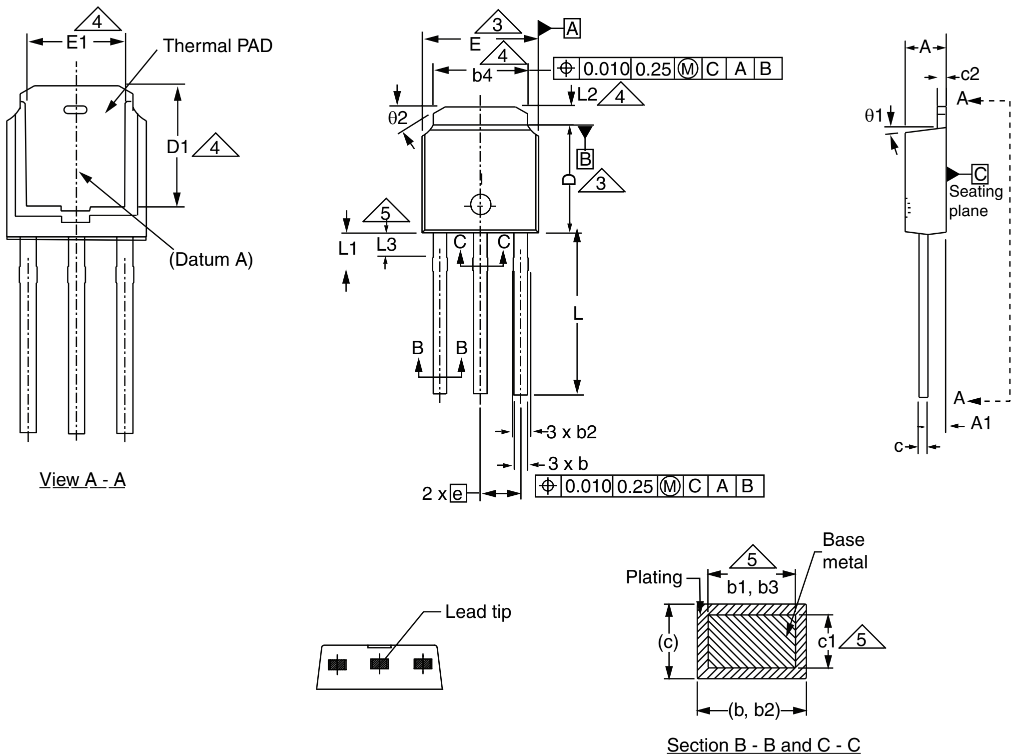


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347				

Notes

- Dimension L3 is for reference only.

TO-251AA (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	0.89	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b1	0.65	0.79	0.026	0.031
b2	0.76	1.14	0.030	0.045
b3	0.76	1.04	0.030	0.041
b4	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c1	0.41	0.56	0.016	0.022
c2	0.46	0.86	0.018	0.034
D	5.97	6.22	0.235	0.245

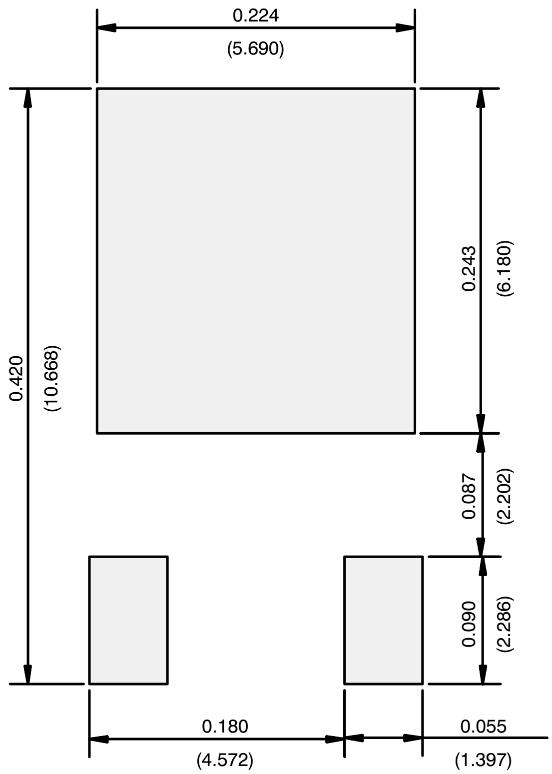
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
e	2.29 BSC		2.29 BSC	
L	8.89	9.65	0.350	0.380
L1	1.91	2.29	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.14	1.52	0.045	0.060
θ1	0'	15'	0'	15'
θ2	25'	35'	25'	35'

ECN: S-82111-Rev. A, 15-Sep-08
DWG: 5968

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension are shown in inches and millimeters.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions b4, L2, E1 and D1.
5. Lead dimension uncontrolled in L3.
6. Dimension b1, b3 and c1 apply to base metal only.
7. Outline conforms to JEDEC outline TO-251AA.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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